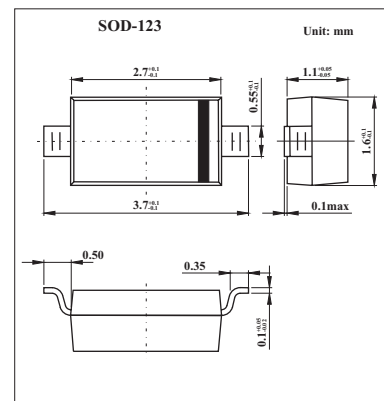


BB721

■ Features

- Silicon epitaxial planar capacitance diodes with very wide effective capacitance variation for tuning the whole range of UHF television bands.
- These diodes are available as singles or as matched sets of two or more units according to the tracking condition described in the table of characteristics.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	32	V
Ambient Temperature	T _{amb}	125	°C
Storage Temperature Range	T _s	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR(R)}	I _R = 100 μA	32			V
Leakage Current	I _R	V _R = 30 V			10	nA
Capacitance	C _{tot}	f = 1 MHz; V _R = 28 V	1.9		2.3	pF
		f = 1 MHz; V _R = 1 V	17.5		20	
Effective Capacitance Ratio	C _{d(1V)} /C _{d(28V)}	f = 1 MHz; V _R = 1 to 28 V	8.2		9.8	
Series Resistance	r _s	f = 470 MHz, C _{tot} = 14 pF		0.55		Ω
Series Inductance	L _s			2.5		nH